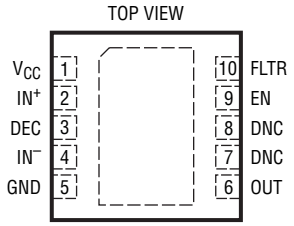
## ABSOLUTE MAXIMUM RATINGS

**(Note 1)**

Supply Voltage ..... 5.5V
Enable Voltage ..... –0.3V to $V_{CC}$ + 0.3V
Input Signal Power (Differential) ..... 15dBm
$T_{JMAX}$ ..... 125°C
Operating Temperature Range ..... –40°C to 85°C
Storage Temperature Range ..... –65°C to 125°C

CAUTION: This part is sensitive to electrostatic discharge. It is very important that proper ESD precautions be observed when handling the LT5570.

## PIN CONFIGURATION




DD PACKAGE
10-LEAD (3mm × 3mm) PLASTIC DFN

$T_{JMAX}$ = 125°C, $\theta_{JA}$ = 43°C/W
EXPOSED PAD (PIN 11) IS GND, MUST BE SOLDERED TO PCB

## ORDER INFORMATION

| LEAD FREE FINISH | TAPE AND REEL | PART MARKING | PACKAGE DESCRIPTION | TEMPERATURE RANGE |
|---|---|---|---|---|
| LT5570IDD#PBF | LT5570IDD#TRPBF | LCJQ | 10-Lead (3mm × 3mm) Plastic DFN | –40°C to 85°C |

Consult LTC Marketing for parts specified with wider operating temperature ranges.
Consult LTC Marketing for information on non-standard lead based finish parts.

For more information on lead free part marking, go to: http://www.linear.com/leadfree/
For more information on tape and reel specifications, go to: http://www.linear.com/tapeandreel/

## ELECTRICAL CHARACTERISTICS

**The ● denotes the specifications which apply over the full operating temperature range, otherwise specifications are at $T_A$ = 25°C, $V_{CC}$ = 5V, EN = 5V, unless otherwise noted. Test circuits are shown in Figures 1 and 3. (Notes 2 and 3).**

| PARAMETER | CONDITIONS | | MIN | TYP | MAX | UNITS |
|---|---|---|---|---|---|---|
| **AC Input** | | | | | | |
| Input Frequency Range (Note 4) | | ● | | 40 to 2700 | | MHz |
| Input Impedance | | | | 200/1 | | Ω/pF |
| **$f_{RF}$ = 500MHz** | | | | | | |
| RF Input Power Range | CW Input; 1:4 Balun Matched into 50Ω Source | | | –52 to 13 | | dBm |
| Linear Dynamic Range (Note 5) | ±1dB Linearity Error, $T_A$ = –40°C to 85°C | | | 62 | | dB |
| Output Slope | | | | 36.9 | | mV/dB |
| Logarithmic Intercept | | | | –54.8 | | dBm |
| Output Variation vs Temperature | Normalized to Output at 25°C<br>–40°C < $T_A$ < 85°C; $P_{IN}$ = –50dBm to 13dBm | | | ±0.5 | | dB |
| Deviation from CW Response | 11dB Peak to Average Ratio (3-Carrier CDMA2K)<br>12dB Peak to Average Ratio (4-Carrier WCDMA) | | | 0.4<br>0.3 | | dB<br>dB |
| 2nd Order Harmonic Distortion | At RF Input; CW Input; $P_{IN}$ = 10dBm | | | 61 | | dBc |
| 3rd Order Harmonic Distortion | At RF Input; CW Input; $P_{IN}$ = 10dBm | | | 66 | | dBc |

## ELECTRICAL CHARACTERISTICS

**The ● denotes the specifications which apply over the full operating temperature range, otherwise specifications are at $T_A$ = 25°C, $V_{CC}$ = 5V, EN = 5V, unless otherwise noted. Test circuits are shown in Figures 1 and 3. (Notes 2 and 3).**

| PARAMETER | CONDITIONS | | MIN | TYP | MAX | UNITS |
|---|---|---|---|---|---|---|
| **$f_{RF}$ = 880MHz** | | | | | | |
| RF Input Power Range | CW Input; 1:4 Balun Matched into 50Ω Source | | | –48 to 13 | | dBm |
| Linear Dynamic Range (Note 5) | ±1dB Linearity Error, $T_A$ = –40°C to 85°C | | | 61 | | dB |
| Output Slope | | | | 37.7 | | mV/dB |
| Logarithmic Intercept | | | | –51.9 | | dBm |
| Output Variation vs Temperature | Normalized to Output at 25°C<br>–40°C < $T_A$ < 85°C; $P_{IN}$ = –47dBm to 13dBm | | | ±0.4 | | dB |
| Deviation from CW Response | 11dB Peak to Average Ratio (3-Carrier CDMA2K)<br>12dB Peak to Average Ratio (4-Carrier WCDMA) | | | 0.3<br>0.2 | | dB |
| 2nd Order Harmonic Distortion | At RF Input; CW Input; $P_{IN}$ = 10dBm | | | 60 | | dBc |
| 3rd Order Harmonic Distortion | At RF Input; CW Input; $P_{IN}$ = 10dBm | | | 61 | | dBc |
| **$f_{RF}$ = 2140MHz** | | | | | | |
| RF Input Power Range | CW Input; 1:4 Balun Matched into 50Ω Source | | | –38 to 13 | | dBm |
| Linear Dynamic Range (Note 5) | ±1dB Linearity Error, $T_A$ = –40°C to 85°C | | 47 | 51 | | dB |
| Output Slope | | | 34.8 | 36.5 | 39.0 | mV/dB |
| Logarithmic Intercept | | | –43.6 | –40.6 | –37.6 | dBm |
| Output Variation vs Temperature | Normalized to Output at 25°C<br>–40°C < $T_A$ < 85°C; $P_{IN}$ = –36dBm to 13dBm | | | ±0.3 | | dB |
| Deviation from CW Response | 11dB Peak to Average Ratio (3-Carrier CDMA2K)<br>12dB Peak to Average Ratio (4-Carrier WCDMA) | | | 0.1<br>0.2 | | dB<br>dB |
| **$f_{RF}$ = 2700MHz** | | | | | | |
| RF Input Power Range | CW Input; 1:4 Balun Matched into 50Ω Source | | | –35 to 13 | | dBm |
| Linear Dynamic Range (Note 5) | ±1dB Linearity Error, $T_A$ = –40°C to 85°C | | | 48 | | dB |
| Output Slope | | | | 36.4 | | mV/dB |
| Logarithmic Intercept | | | | –38.5 | | dBm |
| Output Variation vs Temperature | Normalized to Output at 25°C<br>–40°C < $T_A$ < 85°C; $P_{IN}$ = –31dBm to 13dBm | | | ±0.2 | | dB |
| Deviation from CW Response | 11dB Peak to Average Ratio (3-Carrier CDMA2K)<br>12dB Peak to Average Ratio (4-Carrier WCDMA) | | | 0.1<br>0.5 | | dB |
| **Output** | | | | | | |
| Output DC Voltage | No RF Signal Present | | | 0.1 | | V |
| Output Impedance | | | | 100 | | Ω |
| Sourcing/Sinking | | | | 5/2.5 | | mA |
| Rise Time | 0.2V to 1.6V, 10% to 90%, C1 = 22nF, $f_{RF}$ = 2140MHz | | | 0.5 | | µS |
| Fall Time | 1.6V to 0.2V, 90% to 10%, C1 = 22nF, $f_{RF}$ = 2140MHz | | | 8 | | µS |

## ELECTRICAL CHARACTERISTICS

**The ● denotes the specifications which apply over the full operating temperature range, otherwise specifications are at $T_A$ = 25°C, $V_{CC}$ = 5V, EN = 5V, unless otherwise noted. Test circuits are shown in Figures 1 and 3. (Notes 2 and 3).**

| PARAMETER | CONDITIONS | | MIN | TYP | MAX | UNITS |
|---|---|---|---|---|---|---|
| **Enable (EN) Low = Off, High = On** | | | | | | |
| EN Input High Voltage (On) | | ● | 2 | | | V |
| EN Input Low Voltage (Off) | | ● | | | 1 | V |
| Enable Pin Input Current | EN = 5V | ● | | 68 | | µA |
| Turn ON Time | $V_{OUT}$ within 10% of Final Value, C1 = 22nF | | | 1 | | µs |
| Turn OFF Time | $V_{OUT}$ < 0.1V, C1 = 22nF | | | 5 | | µs |
| **Power Supply** | | | | | | |
| Supply Voltage | | ● | 4.75 | 5 | 5.25 | V |
| Supply Current | | | | 26.5 | 32.5 | mA |
| Shutdown Current | EN = 0V, $V_{CC}$ = 5V | | | 0.1 | 100 | µA |

**Note 1:** Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

**Note 2:** Specifications over the –40°C to +85°C temperature range are assured by design, characterization and correlation with statistical process controls.

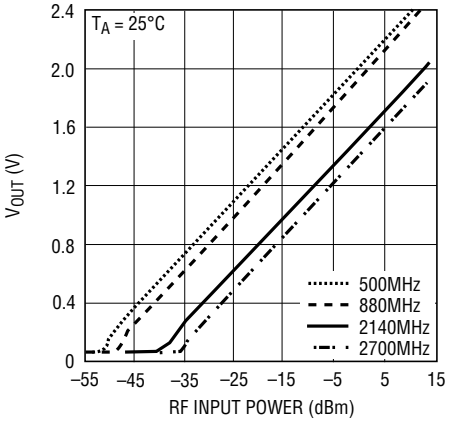
**Note 3:** A 1:4 input transformer is used for the input matching to 50Ω source.

**Note 4:** Operation over a wider frequency range is possible with reduced performance. Consult the factory for information and assistance.

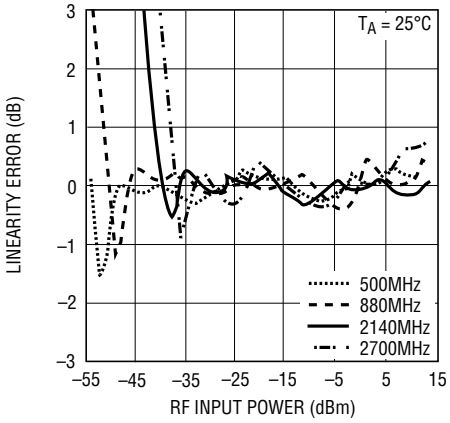
**Note 5:** The linearity error is calculated by the difference between the incremental slope of the output and the average output slope from –30dBm to 2dBm. The dynamic range is defined as the range over which the linearity error is within ±1dB.

## TYPICAL PERFORMANCE CHARACTERISTICS (Test Circuits Shown in Figures 1 and 3)

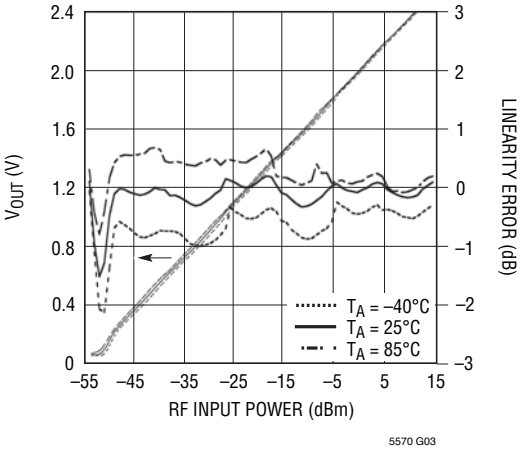
### Output Voltage vs Frequency



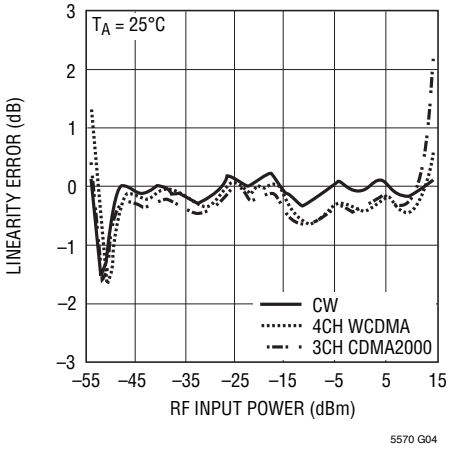

### Linearity Error vs Frequency



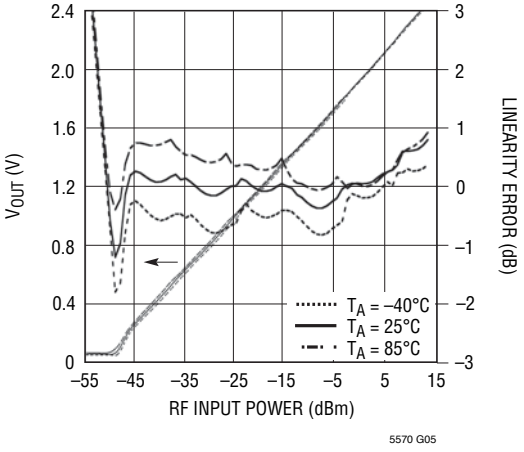

### Output Voltage, Linearity Error vs RF Input Power, 500MHz



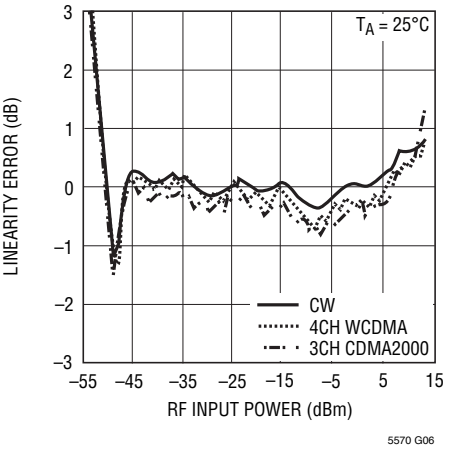

### Linearity Error vs RF Input Power, 500MHz Modulated Waveforms




### Output Voltage, Linearity Error vs RF Input Power, 880MHz

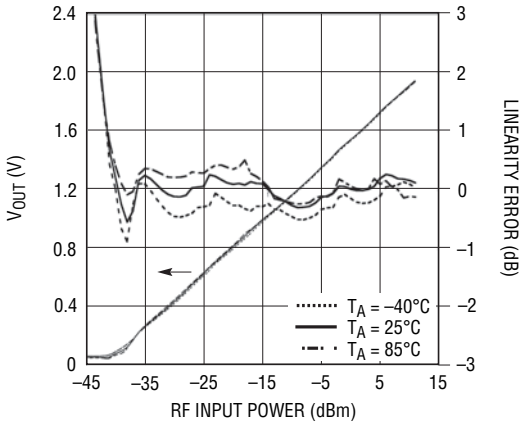



### Linearity Error vs RF Input Power, 880MHz Modulated Waveforms



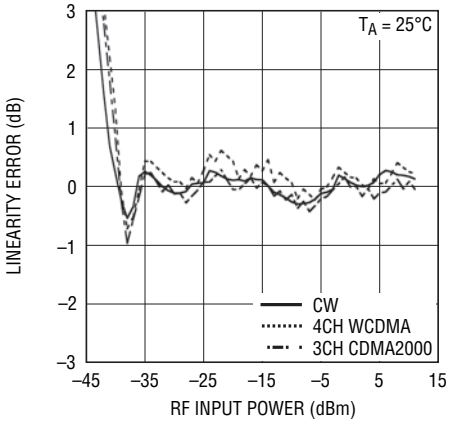
## TYPICAL PERFORMANCE CHARACTERISTICS (Test Circuits Shown in Figures 1 and 3)

**Output Voltage, Linearity Error vs RF Input Power, 2140MHz**



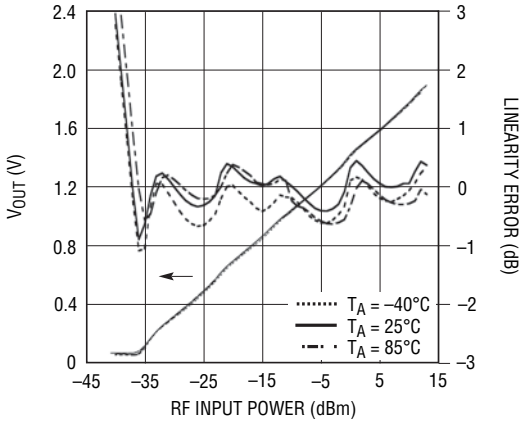

5570 G07

**Linearity Error vs RF Input Power, 2140MHz Modulated Waveforms**



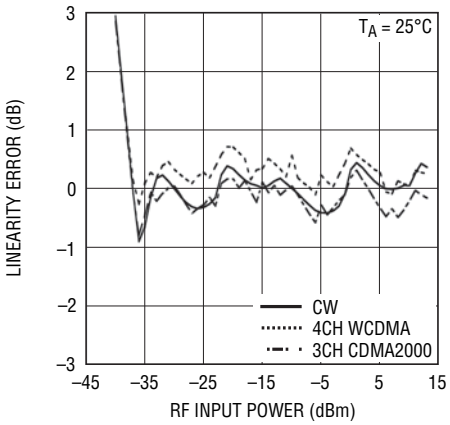

5570 G08

**Output Voltage, Linearity Error vs RF Input Power, 2700MHz**



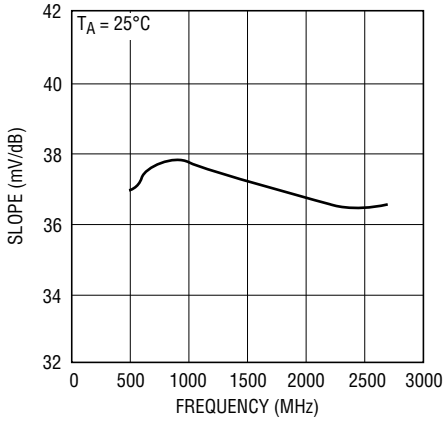

5570 G09

**Linearity Error vs RF Input Power, 2700MHz Modulated Waveforms**



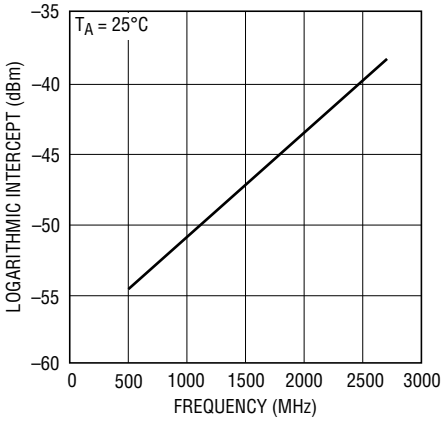

5570 G10

**Slope vs Frequency**




5570 G11

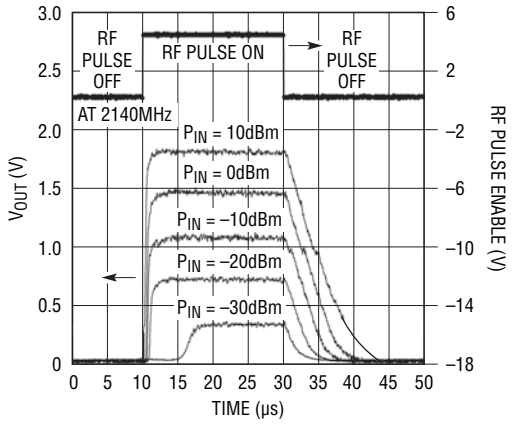
**Logarithmic Intercept vs Frequency**




5570 G12

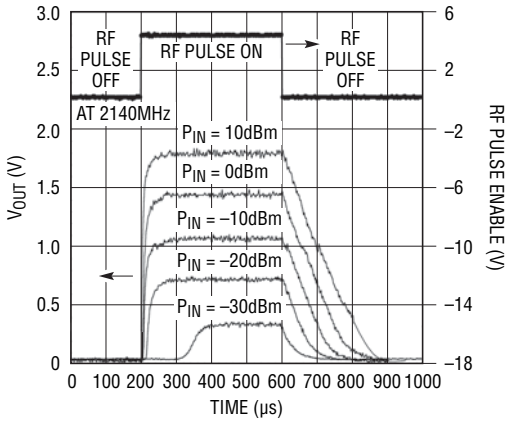
## TYPICAL PERFORMANCE CHARACTERISTICS (Test Circuits Shown in Figures 1 and 3)

### Output Transient Response, C1 = 22nF



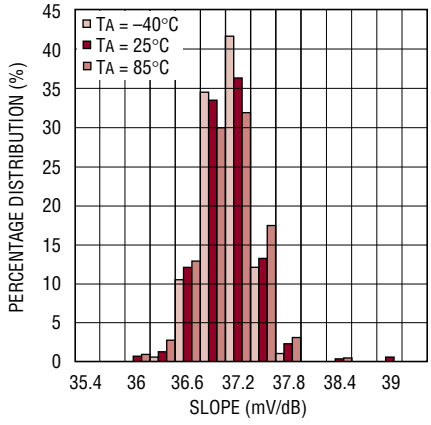

5570 G13

### Output Transient Response, C1 = 1µF



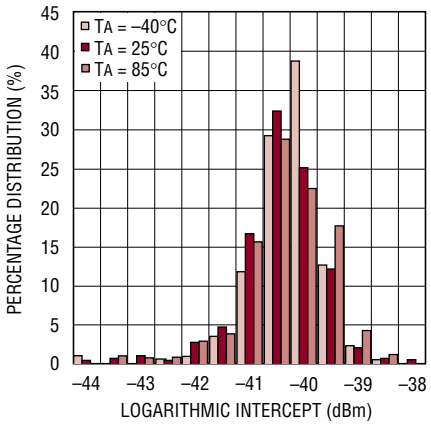

5570 G14

### Slope Distribution vs Temperature



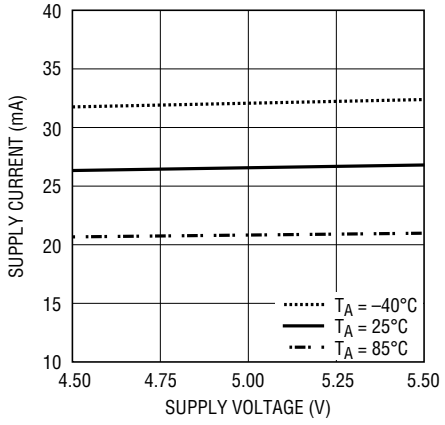

5570 G15

### Logarithmic Intercept Distribution vs Temperature



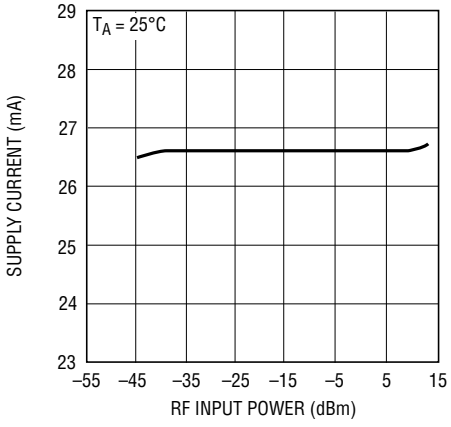

5570 G16

### Supply Current vs Supply Voltage



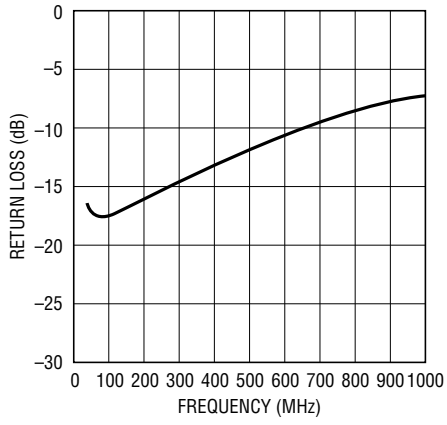

5570 G17

### Supply Current vs RF Input Power



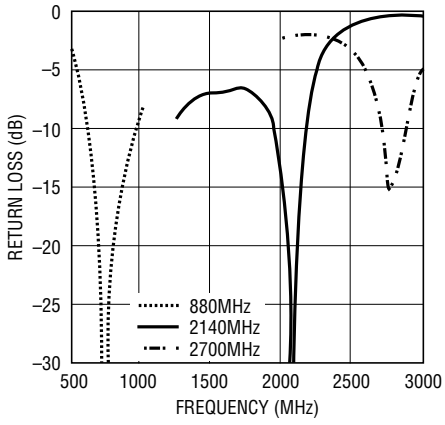

5570 G18

### Input Return Loss vs Frequency Reference in Figure 3




5570 G19

### Input Return Loss vs Frequency Reference in Figure 1




5570 G20

## PIN FUNCTIONS

**$V_{CC}$ (Pin 1):** Power Supply Pin for the Bias Circuits. Typical current consumption is 26.5mA. This pin should be externally bypassed with 1nF and 1µF chip capacitors.

**$IN^+$, $IN^-$ (Pins 2, 4):** Differential Input Signal Pins. These pins are preferably driven with a differential signal for optimum performance. The pins are internally biased to $V_{CC}$ – 1.224V and should be DC blocked externally. The differential impedance is about 200Ω.

**DEC (Pin 3):** Input Common Mode Decoupling Pin. This pin is internally biased to $V_{CC}$ – 1.224V. The input impedance is about 1.75KΩ in parallel with a 10pF internal shunt capacitor to ground. The impedance between DEC and $IN^+$ (or $IN^-$) is about 100Ω. The pin can be connected to the center tap of an external balun. An ac-decoupling capacitor may be connected to ground to maintain the IC performance if necessary.

**GND (Pin 5, Exposed Pad):** Circuit Ground Return for the Entire IC. This must be soldered to the printed circuit board ground plane.

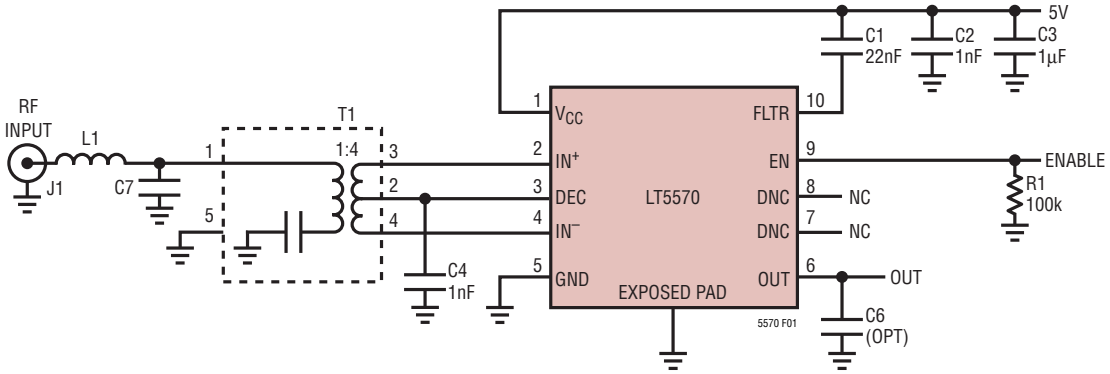
**OUT (Pin 6):** DC Output Pin. The output impedance is mainly determined by an internal 100Ω series resistance that provides output circuit protection if the output is shorted to ground.

**DNC (Pins 7, 8):** Do Not Connect. Don't connect any external component at these pins. Avoid a long wire or metal trace on the PCB.

**EN (Pin 9):** Enable Pin. An applied voltage above 2V will activate the bias for the IC. For an applied voltage below 1V, the circuits will be shut down (disabled) with a corresponding reduction in power supply current. If the enable function is not required, then this pin should be connected to $V_{CC}$. Typical enable pin input current is 68µA for EN = 5V. Note that at no time should the Enable pin voltage be allowed to exceed $V_{CC}$ by more than 0.3V.

**FLTR (Pin 10):** Connection for an External Filtering Capacitor C1. A minimum 22nF capacitor is required for stable ac average power measurement. This capacitor should be connected between Pin 10 and $V_{CC}$.

## TEST CIRCUITS




| REF DES | VALUE | SIZE | PART NUMBER |
|---|---|---|---|
| C2, C4 | 1nF | 0402 | AVX 0402ZC102KAT |
| C1 | 22nF | 0402 | AVX 0402YC223KAT |
| C3 | 1µF | 0603 | Taiyo Yuden LMK107BJ105MA |
| R1 | 100k | 0402 | CRCW0402100KFKED |

| FREQUENCY | T1 | L1 | L1 P/N | C7 | |
|---|---|---|---|---|---|
| 880MHz | MURATA LDB21869M20C-001 | 8.2nH | TOKO LL1005-FH8N25 | 2.7pF | MURATA GRM1555C1H2R7DZ01 |
| 2140MHz | MURATA LDB212G1020-001 | 3.3nH | TOKO LL1005-FH3N35 | 0.5pF | MURATA GRM1555C1HR50CZ01 |
| 2700MHz | MURATA LDB212G4020-001 | 1.2nH | TOKO LL1005-FH1N25 | 1pF | MURATA GRM1555C1H1R0DZ01 |

**Figure 1. Test Schematic for 880MHz, 2140MHz and 2700MHz Applications**

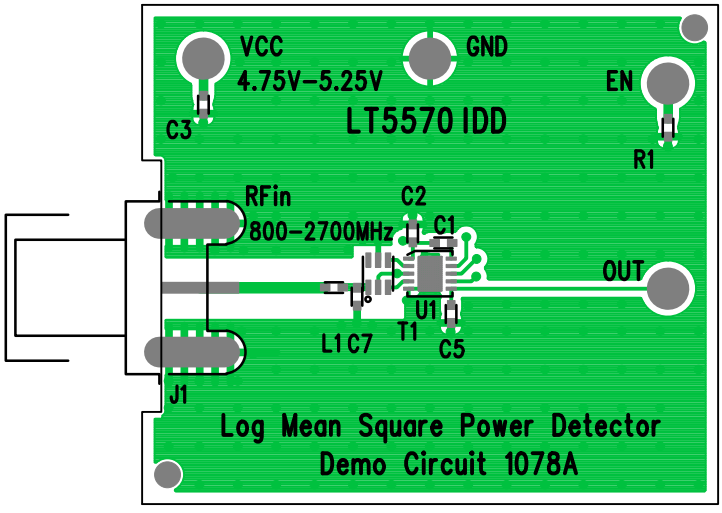
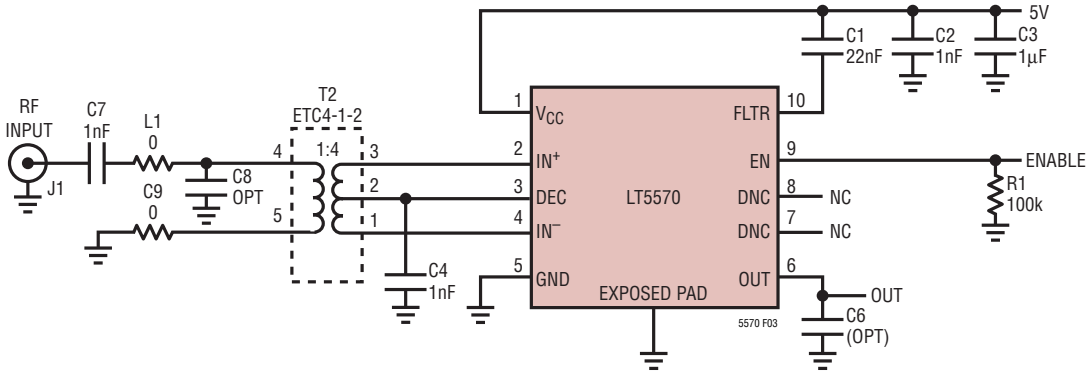



**Figure 2. Top Side of Evaluation Board for 880MHz, 2140MHz and 2700MHz Applications**

## TEST CIRCUITS




| REF DES | VALUE | SIZE | PART NUMBER |
|---|---|---|---|
| C2, C4, C7 | 1nF | 0402 | AVX 0402ZCI02KAT |
| C1 | 22nF | 0402 | AVX 0402YC223KAT |
| C3 | 1µF | 0603 | Taiyo Yuden LMK107BJ105MA |

| REF DES | VALUE | SIZE | PART NUMBER |
|---|---|---|---|
| R1 | 100k | 0402 | CRCW0402100KFKED |
| T2 | 1:4 | | ETC4-1-2 |
| C8 | OPT | 0402 | |
| C9, L1 | 0 | 0402 | CJ05-000M |

**Figure 3. Test Schematic for 40MHz to 860MHz Applications**

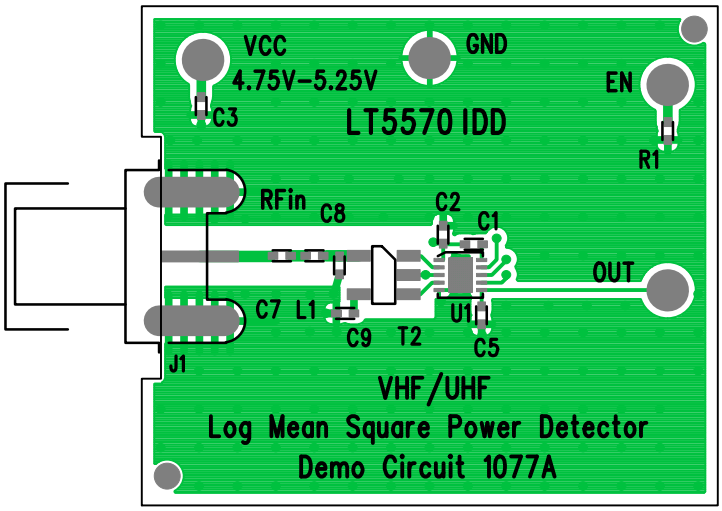



**Figure 4. Top Side of Evaluation Board for 40MHz to 860MHz Applications**

## APPLICATIONS INFORMATION

The LT5570 is a mean-squared RF power detector, capable of measuring an RF signal over the frequency range from 40MHz to 2.7GHz, independent of input waveforms with different crest factors such as CW, CDMA, WCDMA, TD-SCDMA and WiMAX signals. A wide dynamic range is achieved with very stable output within the full temperature range from –40°C to 85°C.

### RF Inputs

The differential RF inputs are internally biased at $V_{CC}$ – 1.224V. The differential impedance is about 200Ω. These pins should be DC blocked when connected to ground or other matching components. The impedance vs. frequency of the differential RF input is detailed in the following table.

**Table 1. RF Differential Input Impedance**

| FREQUENCY (MHz) | DIFFERENTIAL INPUT IMPEDANCE (Ω) | S11 | |
|---|---|---|---|
| | | MAG | ANGLE (°) |
| 40 | 204 –j 0.6 | 0.606 | –0.1 |
| 100 | 204 –j 1.8 | 0.606 | –0.3 |
| 200 | 204 –j 3.6 | 0.606 | –0.5 |
| 400 | 203.5 –j 7.3 | 0.606 | –1.1 |
| 600 | 202.8 –j 10.9 | 0.605 | –1.6 |
| 800 | 201.8 –j 14.5 | 0.604 | –2.1 |
| 1000 | 200.6 –j17.9 | 0.603 | –2.7 |
| 1200 | 199.1 –j21.3 | 0.602 | –3.2 |
| 1400 | 197.3 –j24.7 | 0.601 | –3.8 |
| 1600 | 195.4 –j27.9 | 0.599 | –4.4 |
| 1800 | 193.2 –j31.1 | 0.598 | –5.0 |
| 2000 | 190.8 –j34.2 | 0.596 | –5.6 |
| 2200 | 188.2 –j37.4 | 0.593 | –6.2 |
| 2400 | 185.3 –j40.4 | 0.591 | –6.9 |
| 2600 | 181.9 –j43.5 | 0.589 | –7.6 |
| 2800 | 178.3 –j46.4 | 0.586 | –8.4 |
| 3000 | 174.4 –j49.3 | 0.582 | –9.2 |

The LT5570's differential inputs are optimally driven from a fully balanced source. When the signal is from a single-ended 50Ω source, conversion to a differential signal is required to achieve the maximum dynamic range. This is best achieved using a 1:4 balun to match the internal 200Ω input impedance as shown in Figures 1 and 3. This impedance transformation results in 6dB voltage gain. At high frequency, additional LC elements may be needed for input impedance matching due to the parasitics of the transformer and PCB trace.

The approximate RF input power range of the LT5570 is 60dB at frequencies up to 900MHz, even with high crest factor signals such as a 4-carrier W-CDMA waveform. However the minimum detectable RF power level degrades as the input RF frequency increases.

Due to the high RF input impedance of the LT5570, a narrow band L-C matching network can be used for the conversion of a single-ended to balanced signal as well. By this means, the sensitivity and overall linear dynamic range of the detector remain the same, without using an RF balun.

The LT5570 can also be driven in a single-ended configuration. Figure 5 shows the simplified circuit of this single-ended configuration. The DEC Pin is preferably ac-coupled to ground via a capacitor rather than left floating.

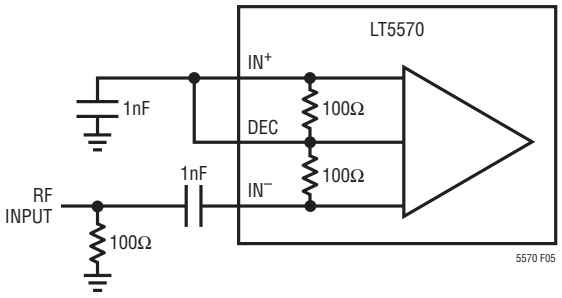



**Figure 5. Single-Ended Input Configuration**

## APPLICATIONS INFORMATION

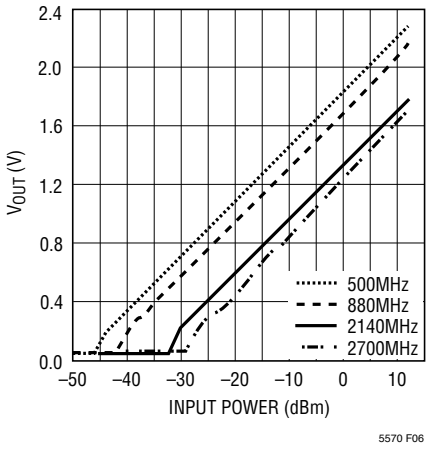



**Figure 6. Output Voltage and Linearity Error vs RF Input Power in Single-ended Input Configuration**

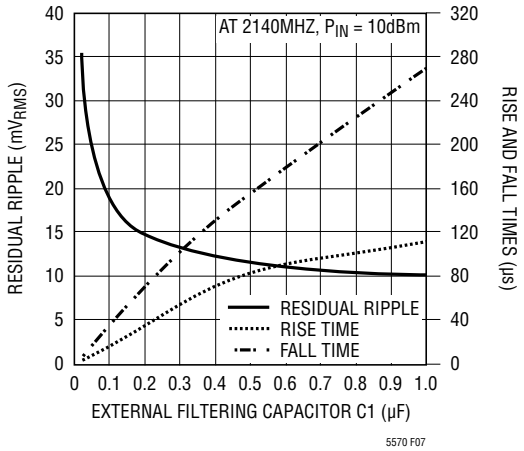



**Figure 7. Residual Ripple, Output Transient Times vs. Filtering Capacitor C1**

The DEC pin can be tied to the IN+ (or IN–) Pin directly and ac-coupled to ground while the RF signal is applied to the IN– (or IN+) Pin. By simply terminating the signal side of the inputs with a 100Ω resistor to ground in front of the ac-blocking capacitor and coupling the other side to ground using a 1nF capacitor, a broadband 50Ω input match can be achieved with typical input return loss better than 12dB from 40MHz to 2.7GHz.

Since there is no voltage conversion gain from impedance transformation in this case, the sensitivity of the detector is reduced by 6dB. The linear dynamic range is reduced by the same amount correspondingly as shown in Figure 6.

### External Filtering (FLTR) Capacitor C1

This pin is internally biased at $V_{CC}$ – 0.13V via a 2k resistor from voltage supply $V_{CC}$. To assure stable operation of the LT5570, an external capacitor C1 with a value of 22nF or higher is required to connect the FLTR Pin to $V_{CC}$. Don't connect this filtering capacitor to ground or any other low voltage reference at any time to avoid an abnormal start-up condition.

C1's value has a dominant effect on the output transient response. The lower the capacitance, the faster the output rise and fall times as illustrated in Figure 7. For signals with AM content such as W-CDMA, ripple can be observed when the loop bandwidth set by C1 is close to the modulation bandwidth of the signal. A 4-carrier W-CDMA RF signal is used as an example in this case. The trade-offs of residual ripple vs. output transient time are also as shown in Figure 7.

In general, the LT5570 output ripple remains relatively constant regardless of the RF input power level for a fixed C1 and modulation format of the RF signal. Typically, C1 must be selected to average out the ripple to achieve the desired accuracy of RF power measurement. For a two-tone RF signal with equal power applied to the LT5570 input, Figure 8 shows the variation of the output dc voltage and its RMS value of the residual ac voltage as a function of the delta frequency. Both values are referred to dB by normalizing them to the output slope (about 37mV/dB). In this measurement, C1 = 22nF. Increasing C1 will shift both curves toward a lower frequency.

## APPLICATIONS INFORMATION

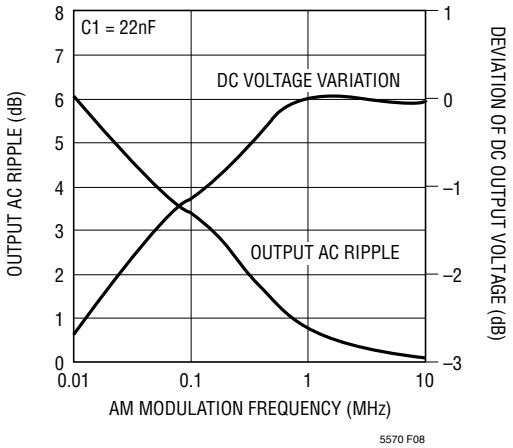



**Figure 8. Output DC Voltage Variation and Residual Ripple vs AM Modulation Frequency**

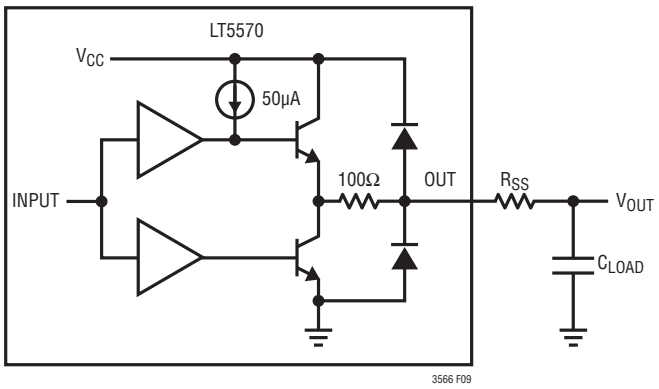



**Figure 9. Simplified Circuit Schematic of the Output Interface**

The high performance RF circuits inside the LT5570 enable it to handle output ripple as high as 2dB without losing its power detection accuracy. The ripple can be further reduced for optimal transient time with an additional RC lowpass filter at the output as discussed in the next section.

### Output Interface

The output buffer amplifier of the LT5570 is shown in Figure 9. This push-pull buffer amplifier can source 5mA current to the load and sink 2.5mA current from the load. The output impedance is determined primarily by the 100Ω series resistor connected to the buffer amplifier. This will prevent any over-stress on the internal devices in case the output is shorted to ground.

The –3dB bandwidth of the buffer amplifier is about 2.4MHz and the full-scale rise/fall time can be as fast as 175ns. When the output is resistively terminated or open, the fastest output transient response is achieved when a large signal is applied to the RF input port. The total rise time of the LT5570 is about 0.5µs and the total fall time is 8µs, respectively, for full-scale pulsed RF input power. The speed of the output transient response is dictated mainly by the filtering capacitor C1 (at least 22nF) at the FLTR pin. See the detailed output transient response in the Typical Performance Characteristics section. When the RF input has AM content, residual ripple may be present at the output depending upon the low frequency content of the modulated RF signal. For example, when 4-carrier WCDMA is applied at the RF input, $\pm 36mV_{RMS}$ (about ±1dB) ripple is present at the output. This ripple can be reduced with a larger filtering capacitor C1 at the expense of a slower transient response.

## APPLICATIONS INFORMATION

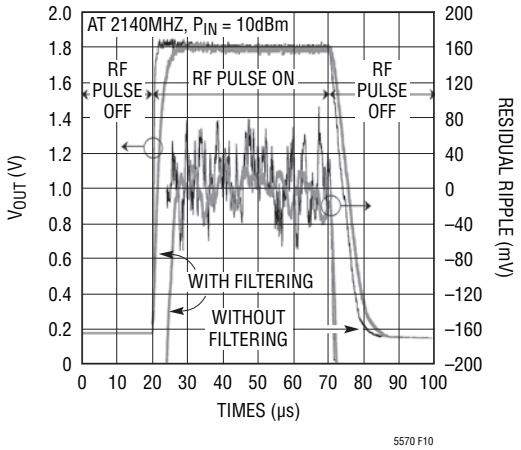



**Figure 10. Residual ripple, Output Transient Times with Output Low-pass Filter**

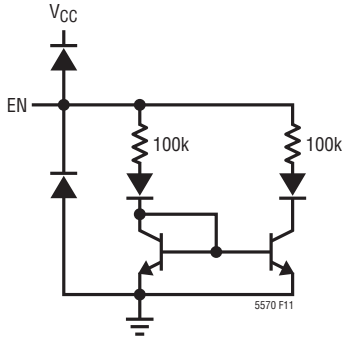



**Figure 11. Enable Pin Simplified Circuit**

Since the output amplifier of the LT5570 is capable of driving an arbitrary capacitive load, the residual ripple can be filtered at the output with a series resistor $R_{SS}$ and a large shunt capacitor $C_{LOAD}$. See Figure 9. This lowpass filter also reduces the output noise by limiting the output noise bandwidth. When this RC network is designed properly, a fast output transient response can be maintained with reduced residual ripple. We can estimate $C_{LOAD}$ with an output voltage swing of 1.8V at 2140MHz. In order that the maximum 2.5mA sinking current not limit the fall time (about 8µS), $C_{LOAD}$ can be chosen as follows.

$C_{LOAD}$ = 2.5mA • approximate additional time/1.8V
= 2.5mA • 0.25µs/1.8V = 347pF

Once $C_{LOAD}$ is determined, $R_{SS}$ can be chosen properly to form a RC lowpass filter with a corner frequency of $2\pi/(R_{SS} \bullet C_{LOAD})$. Using 4-carrier W-CDMA as an example, Figure 10 shows the residual ripple is reduced to half from $36mV_{RMS}$ with $R_{SS}$ = 4.7k and $C_{LOAD}$ = 330pF, while the fall time is slightly increased to 8.8µS.

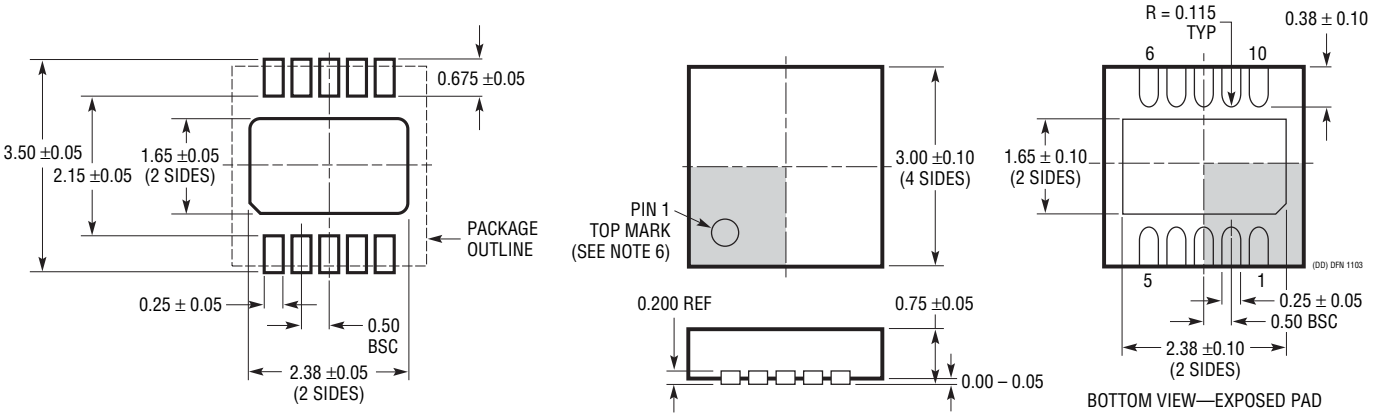
In general, the rise time of the LT5570 is much shorter than the fall time. However, when the output RC filter is used, the rise time is dominated by the time constant of this filter. Accordingly, the rise time becomes very similar to the fall time.

### Enable Interface

A simplified schematic of the EN Pin interface is shown in Figure 11. The enable voltage necessary to turn on the LT5570 is 2V. To disable or turn off the chip, this voltage should be below 1V. It is important that the voltage applied to the EN pin should never exceed $V_{CC}$ by more than 0.3V. Otherwise, the supply current may be sourced through the upper ESD protection diode connected at the EN pin. Under no circumstances should voltage be applied to the EN Pin before the supply voltage is applied to the $V_{CC}$ pin. If this occurs, damage to the IC may result.

# PACKAGE DESCRIPTION

**DD Package**
**10-Lead Plastic DFN (3mm × 3mm)**
(Reference LTC DWG # 05-08-1699)




**RECOMMENDED** SOLDER PAD PITCH AND DIMENSIONS

NOTE:
1. DRAWING TO BE MADE A JEDEC PACKAGE OUTLINE M0-229 VARIATION OF (WEED-2).
   CHECK THE LTC WEBSITE DATA SHEET FOR CURRENT STATUS OF VARIATION ASSIGNMENT
2. DRAWING NOT TO SCALE
3. ALL DIMENSIONS ARE IN MILLIMETERS
4. DIMENSIONS OF EXPOSED PAD ON BOTTOM OF PACKAGE DO NOT INCLUDE
   MOLD FLASH. MOLD FLASH, IF PRESENT, SHALL NOT EXCEED 0.15mm ON ANY SIDE
5. EXPOSED PAD SHALL BE SOLDER PLATED
6. SHADED AREA IS ONLY A REFERENCE FOR PIN 1 LOCATION ON THE
   TOP AND BOTTOM OF PACKAGE

## RELATED PARTS

| PART NUMBER | DESCRIPTION | COMMENTS |
|---|---|---|
| **Infrastructure** | | |
| LT5514 | Ultralow Distortion, IF Amplifier/ADC Driver with Digitally Controlled Gain | 850MHz Bandwidth, 47dBm OIP3 at 100MHz, 10.5dB to 33dB Gain Control Range |
| LT5515 | 1.5GHz to 2.5GHz Direct Conversion Quadrature Demodulator | 20dBm IIP3, Integrated LO Quadrature Generator |
| LT5516 | 0.8GHz to 1.5GHz Direct Conversion Quadrature Demodulator | 21.5dBm IIP3, Integrated LO Quadrature Generator |
| LT5517 | 40MHz to 900MHz Quadrature Demodulator | 21dBm IIP3, Integrated LO Quadrature Generator |
| LT5518 | 1.5GHz to 2.4GHz High Linearity Direct Quadrature Modulator | 22.8dBm OIP3 at 2GHz, –158.2dBm/Hz Noise Floor, 50Ω Single-Ended RF and LO Ports, 4-Channel W-CDMA ACPR = –64dBc at 2.14GHz |
| LT5519 | 0.7GHz to 1.4GHz High Linearity Upconverting Mixer | 17.1dBm IIP3 at 1GHz, Integrated RF Output Transformer with 50Ω Matching, Single-Ended LO and RF Ports Operation |
| LT5520 | 1.3GHz to 2.3GHz High Linearity Upconverting Mixer | 15.9dBm IIP3 at 1.9GHz, Integrated RF Output Transformer with 50Ω Matching, Single-Ended LO and RF Ports Operation |
| LT5521 | 10MHz to 3700MHz High Linearity Upconverting Mixer | 24.2dBm IIP3 at 1.95GHz, NF = 12.5dB, 3.15V to 5.25V Supply, Single-Ended LO Port Operation |
| LT5522 | 600MHz to 2.7GHz High Signal Level Downconverting Mixer | 4.5V to 5.25V Supply, 25dBm IIP3 at 900MHz, NF = 12.5dB, 50Ω Single-Ended RF and LO Ports |
| LT5524 | Low Power, Low Distortion ADC Driver with Digitally Programmable Gain | 450MHz Bandwidth, 40dBm OIP3, 4.5dB to 27dB Gain Control |
| LT5525 | High Linearity, Low Power Downconverting Mixer | Single-Ended 50Ω RF and LO Ports, 17.6dBm IIP3 at 1900MHz, $I_{CC}$ = 28mA |
| LT5526 | High Linearity, Low Power Downconverting Mixer | 3V to 5.3V Supply, 16.5dBm IIP3, 100kHz to 2GHz RF, NF = 11dB, $I_{CC}$ = 28mA, –65dBm LO-RF Leakage |
| LT5527 | 400MHz to 3.7GHz High Signal Level Downconverting Mixer | IIP3 = 23.5dBm and NF = 12.5dBm at 1900MHz, 4.5V to 5.25V Supply, $I_{CC}$ = 78mA, Conversion Gain = 2dB |
| LT5528 | 1.5GHz to 2.4GHz High Linearity Direct Quadrature Modulator | 21.8dBm OIP3 at 2GHz, –159.3dBm/Hz Noise Floor, 50Ω, $0.5V_{DC}$ Baseband Interface, 4-Channel W-CDMA ACPR = –66dBc at 2.14GHz |
| LT5557 | 400MHz to 3.8GHz, 3.3V High Signal Level Downconverting Mixer | IIP3 = 23.7dBm at 2600MHz, 23.5dBm at 3600MHz, $I_{CC}$ = 82mA at 3.3V |
| LT5560 | Ultra-Low Power Active Mixer | 10mA Supply Current, 10dBm IIP3, 10dB NF, Usable as Up- or Down-Converter. |
| LT5568 | 700MHz to 1050MHz High Linearity Direct Quadrature Modulator | 22.9dBm OIP3 at 850MHz, –160.3dBm/Hz Noise Floor, 50Ω, $0.5V_{DC}$ Baseband Interface, 3-Ch CDMA2000 ACPR = –71.4dBc at 850MHz |
| LT5572 | 1.5GHz to 2.5GHz High Linearity Direct Quadrature Modulator | 21.6dBm OIP3 at 2GHz, –158.6dBm/Hz Noise Floor, High-Ohmic $0.5V_{DC}$ Baseband Interface, 4-Ch W-CDMA ACPR = –67.7dBc at 2.14GHz |
| LT5575 | 800MHz to 2.7GHz High Linearity Direct Conversion I/Q Demodulator | 50Ω, Single-Ended RF and LO Inputs. 28dBm IIP3 at 900MHz, 13.2dBm P1dB, 0.04dB I/Q Gain Mismatch, 0.4° I/Q Phase Mismatch |
| **RF Power Detectors** | | |
| LTC®5505 | RF Power Detectors with >40dB Dynamic Range | 300MHz to 3GHz, Temperature Compensated, 2.7V to 6V Supply |
| LTC5507 | 100kHz to 1000MHz RF Power Detector | 100kHz to 1GHz, Temperature Compensated, 2.7V to 6V Supply |
| LTC5508 | 300MHz to 7GHz RF Power Detector | 44dB Dynamic Range, Temperature Compensated, SC70 Package |
| LTC5509 | 300MHz to 3GHz RF Power Detector | 36dB Dynamic Range, Low Power Consumption, SC70 Package |
| LTC5530 | 300MHz to 7GHz Precision RF Power Detector | Precision $V_{OUT}$ Offset Control, Shutdown, Adjustable Gain |
| LTC5531 | 300MHz to 7GHz Precision RF Power Detector | Precision $V_{OUT}$ Offset Control, Shutdown, Adjustable Offset |
| LTC5532 | 300MHz to 7GHz Precision RF Power Detector | Precision $V_{OUT}$ Offset Control, Adjustable Gain and Offset |
| LT5534 | 50MHz to 3GHz Log RF Power Detector with 60dB Dynamic Range | ±1dB Output Variation over Temperature, 38ns Response Time, Log Linear Response |
| LTC5536 | Precision 600MHz to 7GHz RF Power Detector with Fast Comparator Output | 25ns Response Time, Comparator Reference Input, Latch Enable Input, –26dBm to +12dBm Input Range |
| LT5537 | Wide Dynamic Range Log RF/IF Detector | Low Frequency to 1GHz, 83dB Log Linear Dynamic Range |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